Product data sheet

1. General description

Planar passivated SCR with sensitive gate in a SOT223 surface mountable plastic package. This SCR is designed to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Direct triggering from low power drivers and logic ICs
- Surface mountable package

3. Applications

- General purpose switching and phase control
- Ignition circuits, CDI for 2- and 3-wheelers
- Motor control e.g. small kitchen appliances

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage			-	-	200	V
V _{RRM}	repetitive peak reverse voltage			-	-	200	V
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$; Fig. 4; Fig. 5		-	-	8	А
I _{T(AV)}	average on-state current	half sine wave; T _{sp} ≤ 112 °C; <u>Fig. 1</u>		-	-	0.5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{sp} \le 112 \text{ °C}$; Fig. 2; Fig. 3		-	-	0.8	А
Static characte	eristics		,				,
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 9		-	50	200	μA





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	4	A -
2	Α	anode		G sym037
3	G	gate		3
4	А	mb; connected to anode	□1 □2 □3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
MCR08BT1	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

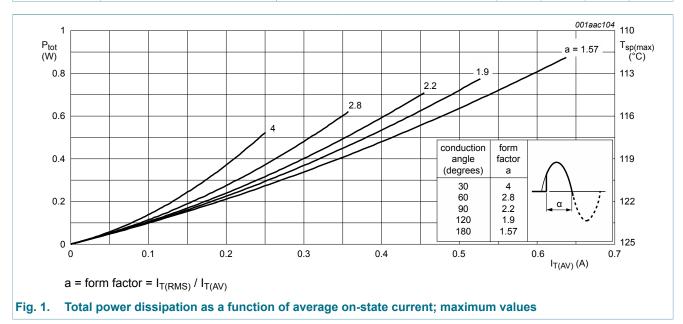
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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	200	V
V_{RRM}	repetitive peak reverse voltage		-	200	V
I _{T(AV)}	average on-state current	half sine wave; T _{sp} ≤ 112 °C; <u>Fig. 1</u>	-	0.5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{sp} \le 112 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	0.8	А
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$; Fig. 4; Fig. 5	-	8	А
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 \text{ms}$	-	9	А
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.32	A ² s
dl _T /dt	rate of rise of on-state current	$I_T = 2 \text{ A}$; $I_G = 10 \text{ mA}$; $dI_G/dt = 100 \text{ mA}/$ µs	-	50	A/µs
I _{GM}	peak gate current		-	1	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



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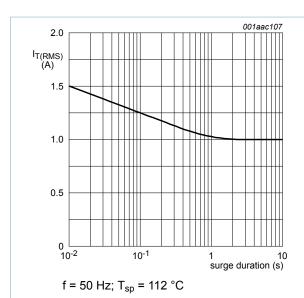


Fig. 2. RMS on-state current as a function of surge duration for sinusoidal currents; maximum values

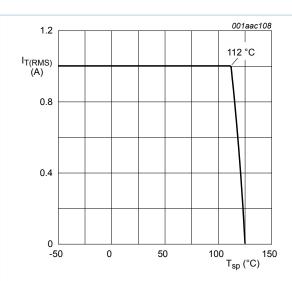


Fig. 3. RMS on-state current as a function of solder point temperature; maximum values

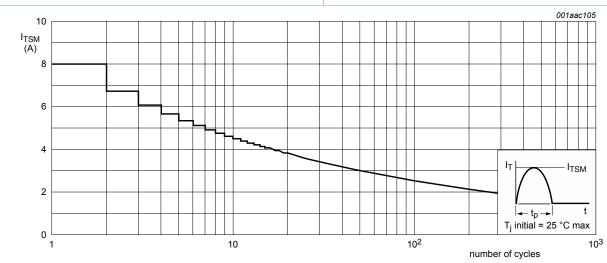
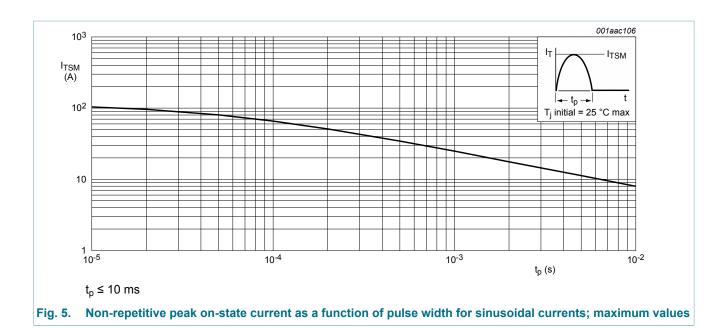


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

f = 50 Hz

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	Fig. 6	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to	printed circuit board mounted; minimum pad area; in free air ; Fig. 7	-	70	-	K/W
	ambient	printed circuit board mounted; minimum footprint; in free air; Fig. 8	-	156	-	K/W

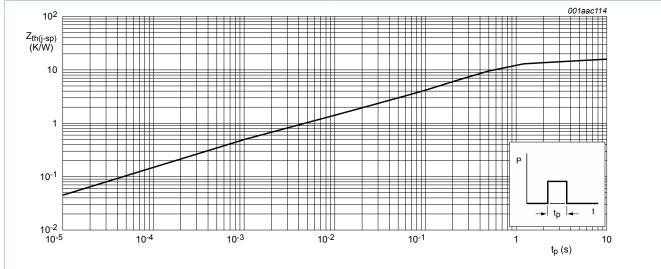
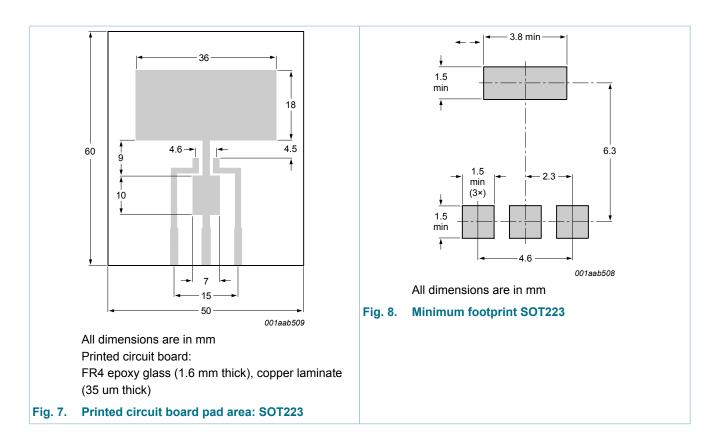


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse duration

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			_
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 10 \text{ mA; } T_j = 25 \text{ °C;}$ Fig. 9	-	50	200	μA
IL	latching current	$V_D = 12 \text{ V; } I_G = 0.5 \text{ mA; } R_{GK} = 1 \text{ k}\Omega;$ $T_j = 25 \text{ °C; } Fig. 10$	-	2	6	mA
l _H	holding current	$V_D = 12 \text{ V}; R_{GK} = 1 \text{ k}\Omega; T_j = 25 \text{ °C};$ Fig. 11	-	2	5	mA
V _T	on-state voltage	I _T = 1.2 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.25	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 10 \text{ mA; } T_j = 25 \text{ °C;}$ Fig. 13	-	0.5	0.8	V
		$V_D = 200 \text{ V}; I_T = 10 \text{ mA}; T_j = 125 °C;$ Fig. 13	0.2	0.3	-	V
I _D	off-state current	$V_D = 200 \text{ V}; T_j = 125 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	0.05	1	mA
I _R	reverse current	$V_R = 200 \text{ V}; T_j = 125 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	0.05	1	mA
Dynamic cl	harateristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 134 V; T_j = 125 °C; R_{GK} = 1 kΩ; (V_{DM} = 67% of V_{DRM}); exponential waveform; Fig. 14	500	800	-	V/µs
		V_{DM} = 134 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14	-	25	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 2 A; V_D = 200 V; I_G = 10 mA; $dI_G/$ dt = 0.1 A/µs; T_j = 25 °C	-	2	-	μs
t _q	commutated turn-off time	$\begin{split} &V_{DM} = 134 \text{ V; } T_j = 125 \text{ °C; } I_{TM} = 1.6 \text{ A;} \\ &V_R = 35 \text{ V; } (dI_T/dt)_M = 30 \text{ A/µs; } dV_D/\\ &dt = 2 \text{ V/µs; } R_{GK} = 1 \text{ k}\Omega; \text{ (V_{DM} = 67\% of V_{DRM})} \end{split}$	-	100	-	μs

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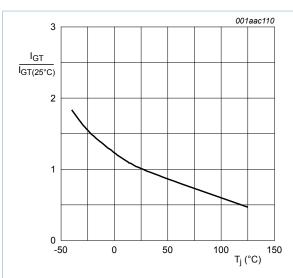


Fig. 9. Normalized gate trigger current as a function of junction temperature

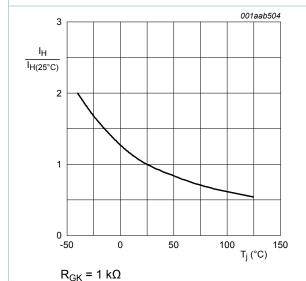
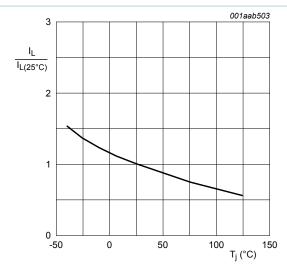
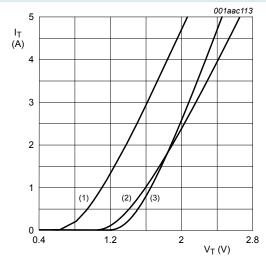


Fig. 11. Normalized holding current as a function of junction temperature



 $R_{GK} = 1 k\Omega$

Fig. 10. Normalized latching current as a function of junction temperature



 $V_0 = 1.0 \text{ V}; R_s = 0.27 \Omega$

(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

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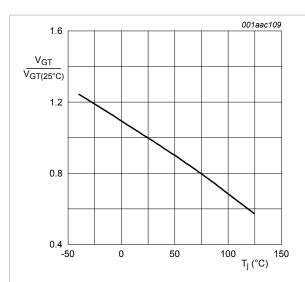
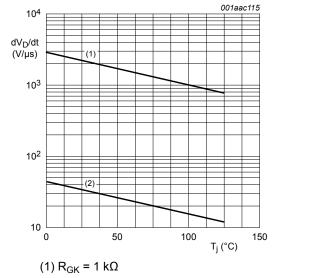


Fig. 13. Normalized gate trigger voltage as a function of junction temperature



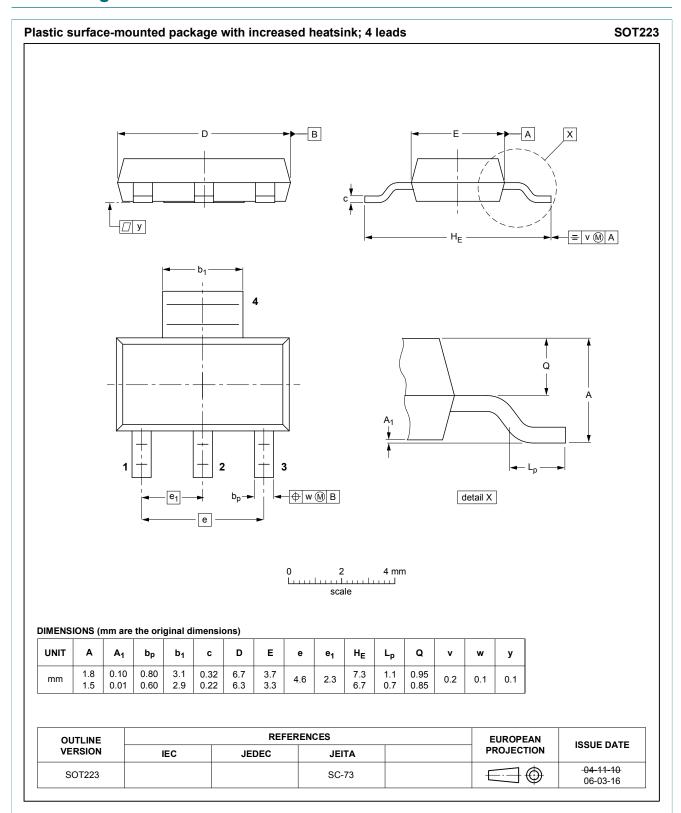
(2) Gate open circuit

Fig. 14. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

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10. Package outline



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11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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